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Raman on graphene Spectral resolution Spatial resolution

Phonon spectrum of graphite



Ref.: Ludger Wirtz and Angel Rubio, Solid State Communications 131, 141 (2004)

- does the phonon spectrum depend on the number of layers ?



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Spatial resolution: AFM



Raman spectra of singleand double layer graphene



Raman mapping: intensity of G-line



two layers have higher G-line intensity, slightly different peak position

Raman mapping: intensity of G-line



Scanning confocal Raman spectroscopy: - Laser excitation of 532 nm/ 2.33 eV - Spot size:





Raman spectra of singleand double layer graphene



Raman mapping: FWHM of the D' line



- Laser excitation of 532 nm/

2.33 eV

- Spot size:



two layers have broader G-line, different peak position

Raman mapping: FWHM of the D' line



Raman: FWHM of D' line



Scanning confocal Raman spectroscopy: - Laser excitation of 532 nm/ 2.33 eV

- Spot size:

two layers have broader G-line, different peak position

D' line for single layer graphene



D' line for double layer graphene

Detecting single layer graphene

What about the D-line?

Raman mapping: intensity of the D line

Double-resonant

close to K, M point, k>0 Momentum restoring: elastic scattering \rightarrow **D**

- 1) Crystallite grain size, symmetry breaking [Tuinstra and Koenig, 1970]
- 2) Defects, disorder in general [Y. Wang et al, 1990]

Raman: Integrated D line intensity

Symmetry breaking and defects

at edges and boundaries,

not within the flake.

Raman mapping: position of D-line

Scanning confocal Raman spectroscopy: - Laser excitation of 532 nm/ 2.33 eV - Spot size:

Raman mapping: intensity of G-line # layers

Raman mapping: relative intensity of G/D'-line

Conclusions

 Raman spectroscopy: an alternative to scanning force microscopy

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- Monolayer sensitivity (single to double layer)
- Defects/symmetry breaking at the edge (not within the flakes)

Raman: Intensity D

D. Graf et al., cond-mat/0607562, submitted Related work: A.C. Ferrari *et al.*, cond-mat/0606284, A. Gupta *et al.*, cond-mat/0606593

Experiment:

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Christoph Stampfer, Alain Jungen, and Christofer Hierold Micro and Nanosystems, ETH Zürich, Switzerland

Theory:

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